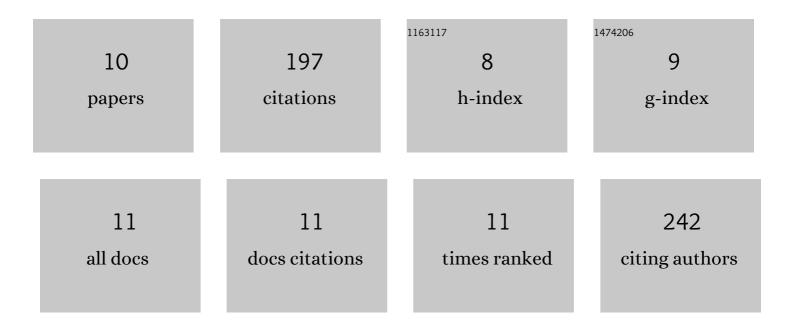
Jiarui Gong

List of Publications by Year in descending order

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IMPLIL CONC

#	Article	IF	CITATIONS
1	226 nm AlGaN/AlN UV LEDs using p-type Si for hole injection and UV reflection. Applied Physics Letters, 2018, 113, .	3.3	59
2	229 nm UV LEDs on aluminum nitride single crystal substrates using p-type silicon for increased hole injection. Applied Physics Letters, 2018, 112, .	3.3	52
3	Reduction of Leakage Current in GaN Schottky Diodes Through Ultraviolet/Ozone Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1796-1799.	3.9	18
4	P-type silicon as hole supplier for nitride-based UVC LEDs. New Journal of Physics, 2019, 21, 023011.	2.9	16
5	AlGaN/GaN Schottky-Gate HEMTs With UV/Oâ, <i>f</i> -Treated Gate Interface. IEEE Electron Device Letters, 2020, 41, 1488-1491.	3.9	13
6	Influences of screw dislocations on electroluminescence of AlGaN/AlN-based UVC LEDs. AIP Advances, 2019, 9, .	1.3	11
7	Fabrication of AlGaAs/GaAs/diamond heterojunctions for diamond-collector HBTs. AIP Advances, 2020, 10, .	1.3	11
8	Metal-Al ₂ O ₃ -GaN capacitors with an ultraviolet/ozone plasma-treated interface. Japanese Journal of Applied Physics, 2020, 59, 030908.	1.5	8
9	Influences of ALD Al ₂ O ₃ on the surface band-bending of c-plane, Ga-face GaN. Japanese Journal of Applied Physics, 2022, 61, 011003.	1.5	7
10	Toward Diamond-Collector Heterojunction Bipolar Transistors via grafted GaAs-Diamond n-p junction. , 2019, , .		2